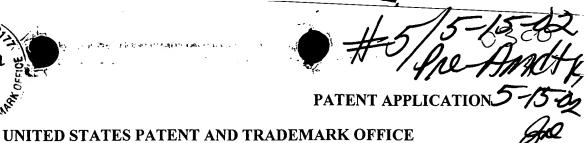


PL!



Group Art Unit: Not Assigned

In re application of

Yoji OKAZAKI, et al.

Appln. No.: 09/987,049

Confirmation No.: 6352

Filed: November 13, 2001 Examiner: Not Assigned

COLOR LASER DISPLAY APPARATUS HAVING FLUORESCENT SCREEN

SCANNED WITH MODULATED ULTRAVIOLET LASER LIGHT

## PRELIMINARY AMENDMENT

Commissioner for Patents Washington, D.C. 20231

Sir:

Prior to examination, please amend the above-identified application as follows:

## IN THE SPECIFICATION:

## Page 26, last paragraph bridging page 27, delete and insert the following:

Figure 14 shows an example of a layering structure of a gallium nitride semiconductor laser having a broad area emission range, listed as 1) above. In the gallium nitride semiconductor laser having this layering structure, an n-type  $Ga_{1-z1}A1_{z1}N/GaN$  super lattice cladding layer 102 (0.05 < z1 < 1), an n-type or i-type GaN optical waveguide layer 104, an  $In_{1-z2}Ga_{z2}N$  (doped with Si)/ $In_{1-z3}Ga_{z3}N$  multiple quantum well active layer 106 (0.01 < z2 < 0.05, 0.1 < z3 < 0.3), a p-type  $Ga_{0.8}A1_{0.2}N$  carrier blocking layer 108, an n-type or i-type GaN photoconductive layer 110, a p-type  $Ga_{1-z1}A1_{z1}N/GaN$  super lattice cladding layer 112, and a p-type GaN contact layer are sequentially layered on an n-type GaN (0001) substrate 100. An insulating film 116 is formed on the p-type GaN contact layer excepting a stripe region with a